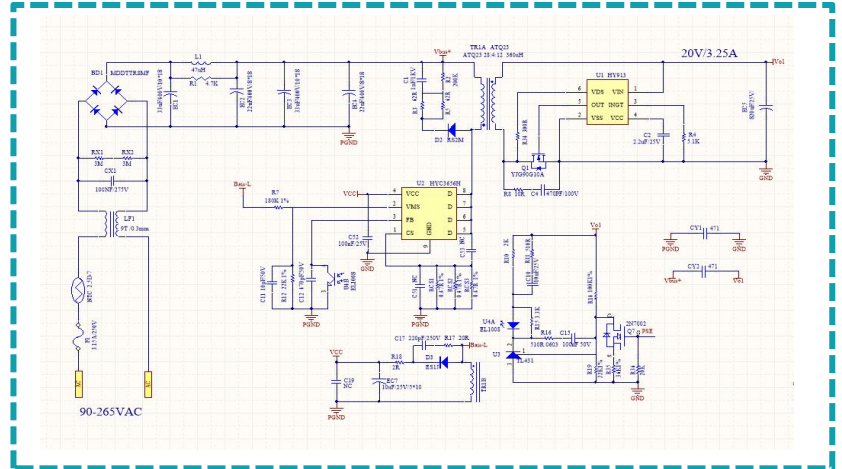


65W-2C1A 合封氮化镓方案

方案特性:

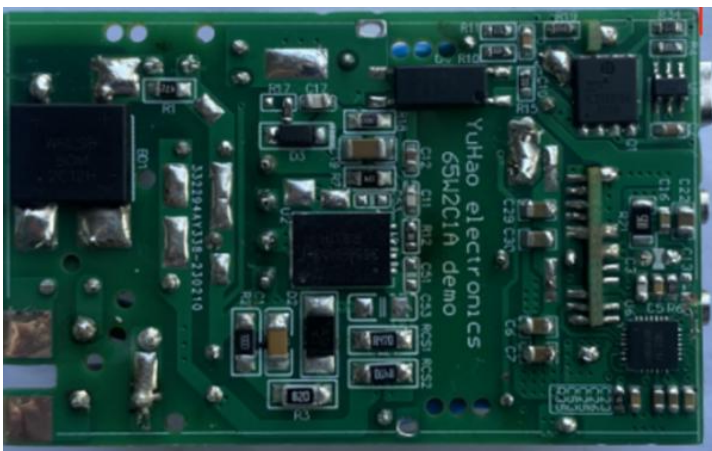
1. 丰富的保护功能确保电源的可靠性
2. 频率抖动降低传导EMI
3. 专利MOSFET驱动改善辐射EMI特性
4. DFN6*8封装
 - 轻松满足目前的COC, DoE, Engerny Star等能效标准
 - 变压器饱和和保护TSP
 - 电流采样电阻短路



PCB顶层



PCB底层



效率测试

V_{IN} (V _{AC})	P_{IN} (W)	V_{OUT} (V)	I_{OUT} (A)	V_{RIPPLE} (mV _{P-P})	P_{OUT} (W)	η (%)	Average η (%)	OCP (A)
90	0.360	20.067	0.000	30			92.01	3.85
	17.82	20.108	0.813	43	16.35	91.74		
	35.45	20.158	1.625	56	32.76	92.40		
	53.33	20.208	2.438	63	49.27	92.38		
	71.91	20.252	3.250	74	65.82	91.53		
115	0.390	20.063	0.000	24			92.76	3.85
	7.44	20.074	0.325	36	6.52	87.69		
	17.78	20.104	0.813	43	16.34	91.93		
	35.19	20.152	1.625	53	32.75	93.06		
	52.86	20.201	2.438	63	49.25	93.17		
230	0.630	20.059	0.000	26			92.48	3.85
	7.80	20.074	0.325	36	6.52	83.64		
	18.12	20.105	0.813	44	16.35	90.21		
	35.36	20.153	1.625	52	32.75	92.61		
	52.75	20.202	2.438	60	49.25	93.37		
264	0.720	20.059	0.000	26			91.95	3.85
	18.30	20.107	0.813	46	16.35	89.33		
	35.60	20.154	1.625	52	32.75	92.00		
	52.91	20.200	2.438	60	49.25	93.08		
	70.46	20.250	3.250	70	65.81	93.40		

65W-2C1A外壳尺寸:
 长65mm*宽43mm*高32mm
整体方案:
 主控IC: HYC3656E
 同步整流: HY913
 协议IC: SW3516+SW3516
 次级MOS: YJG90G10A
 功率分配MCU:P3712